

PROPOSED AMENDMENTS ONLY FOR INTERVIEW WITH EXAMINER PIZARRO-CRESPO ON 12-17-02

1. (Proposed amendment) Integrated circuitry comprising a capacitor comprising a first capacitor electrode, a second capacitor electrode and a high K capacitor dielectric region received therebetween; the high K capacitor dielectric region comprising a high K substantially amorphous material layer and a high K substantially crystalline material layer, the high K substantially amorphous material and the high K substantially crystalline material constituting different chemical compositions, the high K substantially crystalline material being received over the high K substantially amorphous material; and

wherein the high K substantially crystalline material layer is at least 70% crystalline and less than 98% 90% crystalline.

63. (Proposed amendment) Integrated circuitry comprising:
a substrate having insulative material formed over an upper surface the substrate; and
at least two gate structures laterally spaced from one another and formed over the upper surface of the substrate, the two gate structures having uppermost surfaces;
the insulative material formed over the two gate structures and upper surface of the substrate;
an opening formed in the insulative material between the two gate structures;
and
a capacitor comprising:
a first electrode layer formed within the opening and having a portion most proximate and spaced from the upper surface of the substrate, the portion elevationally below the uppermost surfaces of the two gate structures;
a high K dielectric layer formed over the first electrode layer and within the opening; and
a second electrode layer formed over the high K dielectric layer.